

# Ivan I Kravchenko

## List of Publications by Year in descending order

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182  
papers

9,517  
citations

66234

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38300

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183  
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183  
docs citations

183  
times ranked

11273  
citing authors

#	ARTICLE	IF	CITATIONS
1	All-Dielectric Meta-Optics for High-Efficiency Independent Amplitude and Phase Manipulation. <i>Advanced Photonics Research</i> , 2022, 3, .	1.7	10
2	Terahertz bound state in the continuum in dielectric membrane metasurfaces. <i>New Journal of Physics</i> , 2022, 24, 053010.	1.2	3
3	Gold Ion Beam Milled Gold Zero-Mode Waveguides. <i>Nanomaterials</i> , 2022, 12, 1755.	1.9	2
4	Topology-empowered membrane devices for terahertz photonics. <i>Advanced Photonics</i> , 2022, 4, .	6.2	13
5	Demonstration of Large-Size Vertical Ga <sub>2</sub> O <sub>3</sub> Schottky Barrier Diodes. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 41-44.	5.4	38
6	Topology-controlled Polarized Photoluminescence from Rare-earth Doped Nanocrystals. , 2021, , .		0
7	Kilovolt Tri-Gate GaN Junction HEMTs with High Thermal Stability. , 2021, , .		6
8	Large-Scale Metasurfaces Based on Grayscale Nanosphere Lithography. <i>ACS Photonics</i> , 2021, 8, 1824-1831.	3.2	24
9	Large area vertical Ga <sub>2</sub> O <sub>3</sub> Schottky diodes for X-ray detection. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2021, 1013, 165664.	0.7	4
10	Mie-Resonant Membrane Huygens' Metasurfaces. <i>Advanced Functional Materials</i> , 2020, 30, 1906851.	7.8	52
11	Tri-gate GaN junction HEMT. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	29
12	Piezoelectric Actuation of Graphene-Coated Polar Structures. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2020, 67, 2142-2147.	1.7	4
13	Flat optics for image differentiation. <i>Nature Photonics</i> , 2020, 14, 316-323.	15.6	311
14	High-efficiency solar thermophotovoltaic system using a nanostructure-based selective emitter. <i>Solar Energy</i> , 2020, 197, 538-545.	2.9	81
15	To switch or not to switch – a machine learning approach for ferroelectricity. <i>Nanoscale Advances</i> , 2020, 2, 2063-2072.	2.2	12
16	Topological nanophotonics for photoluminescence control. <i>Nanophotonics</i> , 2020, 10, 435-441.	2.9	16
17	Ultra-Sensitive and High Figure of Merit Interferometric Biosensors Using Dispersion Effects in Porous Waveguides. , 2020, , .		1
18	Consideration of temperature-dependent emissivity of selective emitters in thermophotovoltaic systems. <i>Applied Optics</i> , 2020, 59, 5457.	0.9	3

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19	Multifunctional metaoptics based on bilayer metasurfaces. <i>Light: Science and Applications</i> , 2019, 8, 80.	7.7	130
20	Surface-Enhanced Raman Scattering (SERS) Studies of Disc-on-Pillar (DOP) Arrays: Contrasting Enhancement Factor with Analytical Performance. <i>Applied Spectroscopy</i> , 2019, 73, 665-677.	1.2	2
21	Dielectric Broadband Metasurfaces for Fiber Mode Multiplexed Communications. <i>Advanced Optical Materials</i> , 2019, 7, 1801679.	3.6	20
22	Environmental Gating and Galvanic Effects in Single Crystals of Organic-Inorganic Halide Perovskites. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 14722-14733.	4.0	14
23	Nonlinear light generation in topological nanostructures. <i>Nature Nanotechnology</i> , 2019, 14, 126-130.	15.6	187
24	Disorder-Robust Nonlinear Light Generation in Topological Nanostructures. , 2019, , .		1
25	Photonic crystal nanobeam biosensors based on porous silicon. <i>Optics Express</i> , 2019, 27, 9536.	1.7	36
26	Single-mode porous silicon waveguide interferometers with unity confinement factors for ultra-sensitive surface adlayer sensing. <i>Optics Express</i> , 2019, 27, 22485.	1.7	16
27	Noninteracting Multilayer Dielectric Metasurfaces for Multiwavelength Metaoptics. , 2019, , .		0
28	Direct atomic fabrication and dopant positioning in Si using electron beams with active real-time image-based feedback. <i>Nanotechnology</i> , 2018, 29, 255303.	1.3	46
29	Grating-based holographic diffraction methods for X-rays and neutrons: phase object approximation and dynamical theory. <i>Journal of Applied Crystallography</i> , 2018, 51, 68-75.	1.9	2
30	Multilayer Noninteracting Dielectric Metasurfaces for Multiwavelength Metaoptics. <i>Nano Letters</i> , 2018, 18, 7529-7537.	4.5	187
31	Quantum metasurface for multiphoton interference and state reconstruction. <i>Science</i> , 2018, 361, 1104-1108.	6.0	227
32	Dynamic transmission control based on all-dielectric Huygens metasurfaces. <i>Optica</i> , 2018, 5, 787.	4.8	116
33	Label-free detection of Herceptin® using suspended silicon microring resonators. <i>Sensors and Actuators B: Chemical</i> , 2018, 275, 394-401.	4.0	17
34	Zika virus detection using antibody-immobilized disposable cover glass and AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	27
35	Nonlinear Wavefront Control with All-Dielectric Metasurfaces. <i>Nano Letters</i> , 2018, 18, 3978-3984.	4.5	180
36	Transparent Dielectric Metasurfaces for Spatial Mode Multiplexing. <i>Laser and Photonics Reviews</i> , 2018, 12, 1800031.	4.4	37

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37	Shaping the third-harmonic radiation from silicon nanodimers. <i>Nanoscale</i> , 2017, 9, 2201-2206.	2.8	50
38	Edge States and Topological Phase Transitions in Chains of Dielectric Nanoparticles. <i>Small</i> , 2017, 13, 1603190.	5.2	77
39	Metasurface polarization splitter. <i>Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences</i> , 2017, 375, 20160072.	1.6	23
40	Ultrafast charge and energy exchanges at hybrid interfaces involving 2D semiconductors (Conference) Tj ETQq0 0 0 rgBT /Ovrlock 10 T		
41	Quantification of in-contact probe-sample electrostatic forces with dynamic atomic force microscopy. <i>Nanotechnology</i> , 2017, 28, 065704.	1.3	43
42	Surface Modification of Silicon Pillar Arrays To Enhance Fluorescence Detection of Uranium and DNA. <i>ACS Omega</i> , 2017, 2, 7313-7319.	1.6	6
43	Improvement of Ohmic contacts on Ga <sub>2</sub> O <sub>3</sub> through use of ITO-interlayers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017, 35, .	0.6	42
44	Atom-by-atom fabrication by electron beam via induced phase transformations. <i>MRS Bulletin</i> , 2017, 42, 653-659.	1.7	18
45	Ohmic contacts on n-type $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> using AZO/Ti/Au. <i>AIP Advances</i> , 2017, 7, .	0.6	48
46	Dimensionality Effects in FeGe <sub>2</sub> Nanowires: Enhanced Anisotropic Magnetization and Anomalous Electrical Transport. <i>Scientific Reports</i> , 2017, 7, 7126.	1.6	9
47	AlGa <sub>N</sub> /Ga <sub>N</sub> High Electron Mobility Transistor Grown and Fabricated on ZrTi Metallic Alloy Buffer Layers. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, S3078-S3080.	0.9	2
48	Highest efficiency grayscale all-dielectric meta-holograms. , 2017, , .		0
49	Quantum polarization tomography with all-dielectric metasurfaces. , 2017, , .		0
50	Quantum imaging with dielectric metasurfaces for multi-photon polarization tomography. , 2017, , .		2
51	Third-Harmonic Generation from Photonic Topological States in Zigzag Arrays of Silicon Nanodisks. , 2017, , .		2
52	Quantum tomography with all-dielectric metasurfaces. , 2017, , .		1
53	Broadband transparent all-dielectric metasurfaces. , 2017, , .		0
54	Grayscale transparent metasurface holograms. <i>Optica</i> , 2016, 3, 1504.	4.8	290

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55	Lithography-Free Large-Area Metamaterials for Stable Thermophotovoltaic Energy Conversion. <i>Advanced Optical Materials</i> , 2016, 4, 671-676.	3.6	23
56	Evaluation of AlGaIn/GaN high electron mobility transistors grown on ZrTi buffer layers with sapphire substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 051208.	0.6	4
57	Effect of proton irradiation dose on InAlN/GaN metal-oxide semiconductor high electron mobility transistors with Al <sub>2</sub> O <sub>3</sub> gate oxide. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, .	0.6	15
58	Invited Article: Broadband highly efficient dielectric metadevices for polarization control. <i>APL Photonics</i> , 2016, 1, .	3.0	320
59	Retention in Porous Layer Pillar Array Planar Separation Platforms. <i>Analytical Chemistry</i> , 2016, 88, 8741-8748.	3.2	14
60	Performance Characteristics of Bio-Inspired Metal Nanostructures as Surface-Enhanced Raman Scattered (SERS) Substrates. <i>Applied Spectroscopy</i> , 2016, 70, 1432-1445.	1.2	5
61	Ultrafast Dynamics of Metal Plasmons Induced by 2D Semiconductor Excitons in Hybrid Nanostructure Arrays. <i>ACS Photonics</i> , 2016, 3, 2389-2395.	3.2	42
62	Exploring Polarization Rotation Instabilities in Super-tetragonal BiFeO <sub>3</sub> Epitaxial Thin Films and Their Technological Implications. <i>Advanced Electronic Materials</i> , 2016, 2, 1600307.	2.6	9
63	Two-dimensional GaSe/MoSe <sub>2</sub> misfit bilayer heterojunctions by van der Waals epitaxy. <i>Science Advances</i> , 2016, 2, e1501882.	4.7	239
64	Slow light Mach-Zehnder interferometer as label-free biosensor with scalable sensitivity. <i>Optics Letters</i> , 2016, 41, 753.	1.7	52
65	Thickness-dependent charge transport in few-layer MoS <sub>2</sub> field-effect transistors. <i>Nanotechnology</i> , 2016, 27, 165203.	1.3	124
66	Direct Measurement of Optical Force Induced by Near-Field Plasmonic Cavity Using Dynamic Mode AFM. <i>Scientific Reports</i> , 2015, 5, 16216.	1.6	21
67	Effect of proton irradiation energy on AlGaIn/GaN metal-oxide semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 051208.	0.6	9
68	Thickness, humidity, and polarization dependent ferroelectric switching and conductivity in Mg doped lithium niobate. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	17
69	Controlled Nanopatterning of a Polymerized Ionic Liquid in a Strong Electric Field. <i>Advanced Functional Materials</i> , 2015, 25, 805-811.	7.8	13
70	Differentiating Ferroelectric and Nonferroelectric Electromechanical Effects with Scanning Probe Microscopy. <i>ACS Nano</i> , 2015, 9, 6484-6492.	7.3	231
71	Nanopillar Based Enhanced-Fluorescence Detection of Surface-Immobilized Beryllium. <i>Analytical Chemistry</i> , 2015, 87, 6814-6821.	3.2	6
72	All-dielectric metasurfaces. , 2015, , .		0

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73	Optical and infrared properties of glancing angle-deposited nanostructured tungsten films. Optics Letters, 2015, 40, 506.	1.7	1
74	Probing Local Bias-Induced Transitions Using Photothermal Excitation Contact Resonance Atomic Force Microscopy and Voltage Spectroscopy. ACS Nano, 2015, 9, 1848-1857.	7.3	37
75	Bias assisted scanning probe microscopy direct write lithography enables local oxygen enrichment of lanthanum cuprates thin films. Nanotechnology, 2015, 26, 325302.	1.3	1
76	Study of the effects of GaN buffer layer quality on the dc characteristics of AlGaIn/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	0.6	2
77	Nanoscale pillar arrays for separations. Analyst, The, 2015, 140, 3347-3351.	1.7	9
78	Enhanced absorption in two-dimensional materials via Fano-resonant photonic crystals. Applied Physics Letters, 2015, 106, .	1.5	86
79	Degradation mechanisms of Ti/Al/Ni/Au-based Ohmic contacts on AlGaIn/GaN HEMTs. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	0.6	6
80	Large-Scale All-Dielectric Metamaterial Perfect Reflectors. ACS Photonics, 2015, 2, 692-698.	3.2	282
81	Optical diffraction properties of multimicrogratings. Applied Optics, 2015, 54, 1808.	0.9	4
82	Nonlinear Fano-Resonant Dielectric Metasurfaces. Nano Letters, 2015, 15, 7388-7393.	4.5	474
83	Nonlinear Conversion Using Fano-Resonant All-Dielectric Metasurfaces. , 2015, , .		0
84	Dielectric Metasurface Analogue of Electromagnetically Induced Transparency. , 2015, , .		2
85	Improvement of drain breakdown voltage with a back-side gate on AlGaIn/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 042201.	0.6	4
86	On Field-Effect Photovoltaics: Gate Enhancement of the Power Conversion Efficiency in a Nanotube/Silicon-Nanowire Solar Cell. ACS Applied Materials & Interfaces, 2015, 7, 21182-21187.	4.0	11
87	Ion transport and softening in a polymerized ionic liquid. Nanoscale, 2015, 7, 947-955.	2.8	18
88	Effect of low dose $\hat{1}^3$ -irradiation on DC performance of circular AlGaIn/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	20
89	Suspended micro-ring resonator for enhanced biomolecule detection sensitivity. , 2014, , .		5
90	All-dielectric metasurface analogue of electromagnetically induced transparency. Nature Communications, 2014, 5, 5753.	5.8	823

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91	Growth of skyrmionic MnSi nanowires on Si: Critical importance of the SiO <sub>2</sub> layer. Nano Research, 2014, 7, 1788-1796.	5.8	11
92	Effect of Gamma Irradiation on DC Performance of Circular-Shaped AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2014, 61, 205-210.	0.3	1
93	Exploring Local Electrostatic Effects with Scanning Probe Microscopy: Implications for Piezoresponse Force Microscopy and Triboelectricity. ACS Nano, 2014, 8, 10229-10236.	7.3	123
94	Cavitation on Deterministically Nanostructured Surfaces in Contact with an Aqueous Phase: A Small-Angle Neutron Scattering Study. Langmuir, 2014, 30, 9985-9990.	1.6	10
95	Dielectric Meta-Reflectarray for Broadband Linear Polarization Conversion and Optical Vortex Generation. Nano Letters, 2014, 14, 1394-1399.	4.5	877
96	Enhancing the Sensitivity of Label-Free Silicon Photonic Biosensors through Increased Probe Molecule Density. ACS Photonics, 2014, 1, 590-597.	3.2	41
97	Direct Probing of Charge Injection and Polarization-Controlled Ionic Mobility on Ferroelectric LiNbO <sub>3</sub> Surfaces. Advanced Materials, 2014, 26, 958-963.	11.1	49
98	Characteristics of gate leakage current and breakdown voltage of AlGaIn/GaN high electron mobility transistors after postprocess annealing. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, .	0.6	15
99	Controlled Vapor Phase Growth of Single Crystalline, Two-Dimensional GaSe Crystals with High Photoresponse. Scientific Reports, 2014, 4, 5497.	1.6	222
100	A new approach for probing matter in periodic nanoconfinements using neutron scattering. Journal of Applied Crystallography, 2014, 47, 1367-1373.	1.9	4
101	Space- and Time-Resolved Mapping of Ionic Dynamic and Electroresistive Phenomena in Lateral Devices. ACS Nano, 2013, 7, 6806-6815.	7.3	48
102	Probing Local Ionic Dynamics in Functional Oxides at the Nanoscale. Nano Letters, 2013, 13, 3455-3462.	4.5	55
103	Silicon Nanopillars As a Platform for Enhanced Fluorescence Analysis. Analytical Chemistry, 2013, 85, 9031-9038.	3.2	29
104	Realization of an all-dielectric zero-index optical metamaterial. Nature Photonics, 2013, 7, 791-795.	15.6	589
105	The effects of proton irradiation on the reliability of InAlIn/GaN high electron mobility transistors. Proceedings of SPIE, 2013, , .	0.8	1
106	Surface-Induced Orientation Control of CuPc Molecules for the Epitaxial Growth of Highly Ordered Organic Crystals on Graphene. Journal of the American Chemical Society, 2013, 135, 3680-3687.	6.6	125
107	Casimir forces on a silicon micromechanical chip. Nature Communications, 2013, 4, 1845.	5.8	109
108	A robust VACNF platform for electrochemical biosensor. , 2013, , .		3

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109	Effect of buffer structures on AlGaIn/GaN high electron mobility transistor reliability. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 011805.	0.6	16
110	GaN metal-insulator-semiconductor high-electron-mobility transistor with plasma enhanced atomic layer deposited AlN as gate dielectric and passivation. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 052201.	0.6	6
111	Impact of proton irradiation on dc performance of AlGaIn/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 042202.	0.6	23
112	Growth diagram of La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> thin films using pulsed laser deposition. Journal of Applied Physics, 2013, 113, .	1.1	20
113	Dependence on proton energy of degradation of AlGaIn/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	34
114	In Situ Formation of Micron-Scale Li-Metal Anodes with High Cyclability. ECS Electrochemistry Letters, 2013, 3, A4-A7.	1.9	4
115	SnO <sub>2</sub> -gated AlGaIn/GaN high electron mobility transistors based oxygen sensors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	5
116	Effects of semiconductor processing chemicals on conductivity of graphene. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	7
117	Quenching of initial ac susceptibility in single-domain Ni nanobars. Physical Review B, 2012, 85, .	1.1	2
118	Proton irradiation energy dependence of dc and rf characteristics on InAlN/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 041206.	0.6	9
119	Silicon Nanopillars for Field-Enhanced Surface Spectroscopy. ACS Nano, 2012, 6, 2948-2959.	7.3	75
120	Doping-Based Stabilization of the M2 Phase in Free-Standing VO <sub>2</sub> Nanostructures at Room Temperature. Nano Letters, 2012, 12, 6198-6205.	4.5	145
121	UV ozone treatment for improving contact resistance on graphene. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	36
122	Nanotransfer Printing Using Plasma Etched Silicon Stamps and Mediated by in Situ Deposited Fluoropolymer. Journal of the American Chemical Society, 2011, 133, 7722-7724.	6.6	12
123	Nonlinear Phenomena in Multiferroic Nanocapacitors: Joule Heating and Electromechanical Effects. ACS Nano, 2011, 5, 9104-9112.	7.3	69
124	Low-Voltage, Low-Power, Organic Light-Emitting Transistors for Active Matrix Displays. Science, 2011, 332, 570-573.	6.0	466
125	Stamping plasmonic nanoarrays on SERS-supporting platforms. Journal of Raman Spectroscopy, 2011, 42, 1916-1924.	1.2	13
126	Comparison of DC performance of Pt/Ti/Au- and Ni/Au-gated AlGaIn/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 042202.	0.6	3



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127	A half wave retarder made of bilayer subwavelength metallic apertures. Applied Physics Letters, 2011, 98, 151107.	1.5	9
128	Fabrication of InAlAs/InGaAsSb/InGaAs double heterojunction bipolar transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 031205.	0.6	6
129	Improvement of Off-State Stress Critical Voltage by Using Pt-Gated AlGaIn/GaN High Electron Mobility Transistors. Electrochemical and Solid-State Letters, 2011, 14, H264.	2.2	21
130	Effects of proton irradiation on dc characteristics of InAlN/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 061201.	0.6	17
131	Improved Off-State Stress Critical Voltage on AlGaIn/GaN High Electron Mobility Transistors Utilizing Pt/Ti/Au Based Gate Metallization. ECS Transactions, 2011, 41, 63-70.	0.3	3
132	Fabrication and Characterization of Self-Aligned InAlAs/InGaAsSb/InGaAs Double Heterojunction Bipolar Transistors. ECS Transactions, 2011, 41, 117-127.	0.3	0
133	ON-SKY DEMONSTRATION OF A LINEAR BAND-LIMITED MASK WITH APPLICATION TO VISUAL BINARY STARS. Astrophysical Journal, 2010, 715, 1533-1538.	1.6	12
134	Normally-on/off AlN/GaN high electron mobility transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2415-2418.	0.8	5
135	Passivation of AlN/GaN high electron mobility transistor using ozone treatment. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 52-55.	0.6	4
136	Isolation blocking voltage of nitrogen ion-implanted AlGaIn/GaN high electron mobility transistor structure. Applied Physics Letters, 2010, 97, .	1.5	49
137	Optical transmission through double-layer, laterally shifted metallic subwavelength hole arrays. Optics Letters, 2010, 35, 2124.	1.7	16
138	Proton irradiation effects on Sb-based heterojunction bipolar transistors. Journal of Vacuum Science & Technology B, 2009, 27, L33.	1.3	1
139	Development of enhancement mode AlN/GaN high electron mobility transistors. Applied Physics Letters, 2009, 94, .	1.5	49
140	Indium zinc oxide thin films deposited by sputtering at room temperature. Applied Surface Science, 2008, 254, 2878-2881.	3.1	32
141	Ir Diffusion Barriers in Ni/Au Ohmic Contacts to p-Type CuCrO <sub>2</sub> . Journal of Electronic Materials, 2008, 37, 161-166.	1.0	1
142	High temperature Ohmic contacts to p-type GaN for use in light emitting applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2241-2243.	0.8	0
143	RF-sputtered CrB <sub>2</sub> diffusion barrier for Ni/Au Ohmic contacts on p-CuCrO <sub>2</sub> . Applied Surface Science, 2008, 254, 5211-5215.	3.1	2
144	High-Performance Indium Gallium Zinc Oxide Transparent Thin-Film Transistors Fabricated by Radio-Frequency Sputtering. Journal of the Electrochemical Society, 2008, 155, H383.	1.3	94

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145	Stable room temperature deposited amorphous InGaZnO[sub 4] thin film transistors. Journal of Vacuum Science & Technology B, 2008, 26, 959.	1.3	66
146	Ir <sup>+</sup> Au Ohmic Contacts on Bulk, Single-Crystal n-Type ZnO. Journal of the Electrochemical Society, 2007, 154, H161.	1.3	2
147	Nanolithographic patterning of transparent, conductive single-walled carbon nanotube films by inductively coupled plasma reactive ion etching. Journal of Vacuum Science & Technology B, 2007, 25, 348.	1.3	47
148	Influence of the film properties on the plasma etching dynamics of rf-sputtered indium zinc oxide layers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 659-665.	0.9	9
149	W <sub>2</sub> B and CrB <sub>2</sub> diffusion barriers for Ni <sup>+</sup> Au contacts to p-GaN. Applied Physics Letters, 2007, 91, .	1.5	9
150	Ohmic contacts to p-type GaN based on TaN, TiN, and ZrN. Applied Physics Letters, 2007, 90, 212107.	1.5	17
151	Ir-Based Schottky and Ohmic Contacts on n-GaN. Journal of the Electrochemical Society, 2007, 154, H584.	1.3	4
152	Thermal stability of Ohmic contacts to InN. Applied Physics Letters, 2007, 90, 162107.	1.5	7
153	Room-Temperature-Deposited Indium-Zinc Oxide Thin Films with Controlled Conductivity. Electrochemical and Solid-State Letters, 2007, 10, H267.	2.2	11
154	Room temperature deposited indium zinc oxide thin film transistors. Applied Physics Letters, 2007, 90, 232103.	1.5	132
155	Improved Long-Term Thermal Stability At 350 <sup>+</sup> C Of TiB <sub>2</sub> -Based Ohmic Contacts On AlGaN/GaN High Electron Mobility Transistors. Journal of Electronic Materials, 2007, 36, 379-383.	1.0	1
156	Thermal Stability of Nitride-Based Diffusion Barriers for Ohmic Contacts to n-GaN. Journal of Electronic Materials, 2007, 36, 1662-1668.	1.0	1
157	The contribution of valence unstable ytterbium states into kinetic properties of YbNi <sub>2</sub> <sup>x</sup> Ge <sub>2+x</sub> and YbCu <sub>2</sub> <sup>x</sup> Si <sub>2+x</sub> . Journal of Alloys and Compounds, 2006, 425, 54-58.	2.8	0
158	Annealing and measurement temperature dependence of W <sub>2</sub> B <sub>5</sub> -based rectifying contacts to n-GaN. Applied Surface Science, 2006, 252, 5814-5819.	3.1	9
159	Use of TiB <sub>2</sub> diffusion barriers for Ni/Au ohmic contacts on p-GaN. Applied Surface Science, 2006, 253, 1255-1259.	3.1	11
160	ZrB <sub>2</sub> -based Ohmic contacts to p-GaN. Applied Surface Science, 2006, 253, 1934-1938.	3.1	2
161	ZrB <sub>2</sub> Schottky diode contacts on n-GaN. Applied Surface Science, 2006, 253, 2315-2319.	3.1	14
162	Stability of Ti/Al/ZrB <sub>2</sub> /Ti/Au ohmic contacts on n-GaN. Applied Surface Science, 2006, 253, 2340-2344.	3.1	11

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163	ZrB <sub>2</sub> /Pt/Au Ohmic contacts on bulk, single-crystal ZnO. Applied Surface Science, 2006, 253, 2465-2469.	3.1	6
164	Annealing temperature dependence of TiB <sub>2</sub> schottky barrier contacts on n-GaN. Journal of Electronic Materials, 2006, 35, 658-662.	1.0	1
165	Comparison of electrical and reliability performances of TiB <sub>2</sub> -, CrB <sub>2</sub> -, and W <sub>2</sub> B <sub>5</sub> -based Ohmic contacts on n-GaN. Journal of Vacuum Science & Technology B, 2006, 24, 744.	1.3	13
166	Thermally Stable TiB <sub>2</sub> Ohmic Contacts on n-ZnO. Electrochemical and Solid-State Letters, 2006, 9, G164.	2.2	3
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